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(54) Title: MULTICOLOUR LIGHT EMITTING STRUCTURE

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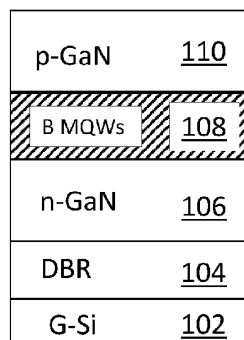


Figure 1A

(57) Abstract: A method of forming a light emitting structure, the light emitting structure comprising: a first light emitting region configured to emit light having a first primary peak wavelength; a second light emitting region configured to emit light having a second primary peak wavelength, wherein the first primary peak wavelength is different to the second primary peak wavelength; and a partially reflective layer positioned at least partially between the first light emitting region and the second light emitting region, wherein the partially reflective layer is configured to reflect light having the first primary peak wavelength emitted by the first light emitting region and allow light having the second primary peak wavelength emitted by the second light emitting region to pass through the partially reflective layer.

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